

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	131	hip and compression with bond\$4 and (silicon semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/27 14:33
L2	18	hip same compression with bond\$4 and (silicon semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/27 14:34
S1	2	("20060240640").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/06/03 13:34
S2	6	((("4124401") or ("5769986") or ("6261927"))).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/06/03 13:37
S3	6	isostatic wafer bond\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2008/06/03 14:04
S4	1192	isostatic bond\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2008/06/03 14:05
S5	1	S4 and (substrate wafer disc)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2008/06/03 14:06
S6	584	S4 and (substrate wafer disc)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:06

S7	198	S6 and clean\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:06
S8	74	S7 and (hydrogen waals)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:32
S9	74	S7 and hydrogen	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:32
S10	1	S7 and waals	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:32
S11	0	S7 and hydrogen near3 termination	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:33
S12	0	S7 and hydrogen near3 termina4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:33
S13	0	S7 and hydrogen near3 termin	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:34
S14	1	S7 and hydrogen near3 termin\$5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:34
S15	153	cleaning with hydrogen near3 termin\$5 near3 surface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:34

S16	137	bond\$4 same (substrate wafer disc)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2008/06/03 14:43
S17	367817	bond\$4 same (substrate wafer disc)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:43
S18	122628	S17 and (heat\$4 and (pressur\$3 pressuriz\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:44
S19	3307	S18 and waals	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:44
S20	2002	S19 and (hydrogen with termin\$5 hydrophobic hf)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:45
S21	9	S20 and isostatic	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:45
S22	266461	bond\$4 with (substrate wafer disc)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:47
S23	1342	S20 and S22	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:47
S24	159690	bond\$4 near3 (substrate wafer disc)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:47

S25	841	S24 and S20	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/03 14:48
S26	2	"20060240640"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/04 09:14
S27	1846	wafer near3 bond\$4 with (pressure compression)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/04 09:35
S28	1391	S27 and temperature	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/04 09:36
S29	1214	S28 and silicon	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/04 09:36
S30	78	S29 and waals	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/04 09:37
S31	1	S30 and isostatic	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/04 09:41
S32	9	S27 and isostatic	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/04 09:42
S33	5	((("6723379") or ("6627814"))).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/06/04 09:44

S34	1888	isostatic adj press	US-PGPUB; USPAT	OR	ON	2008/06/04 09:45
S35	965	hot adj isostatic adj press	US-PGPUB; USPAT	OR	ON	2008/06/04 09:45
S36	10	wafer near3 bond\$4 and S34	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/04 09:45
S37	52	wafer near3 bond\$4 and isostatic	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/04 09:47
S38	55	clean\$4 and S30	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/04 09:50
S39	34	unsealed and isostatic	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/04 11:42
S40	0	gass adj pressure adj bonding with wafer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/06/04 11:44
S41	575768	HIP same bond saem wafer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/30 14:22
S42	7	HIP same bond same wafer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/30 14:22
S43	6	HIP with bond\$3 with wafer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/30 14:23

S44	120	HIP with bond\$3 with substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/30 14:24
S45	111	isostatic with bond\$3 with substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/30 14:28
S46	45	isostatic with wafer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/30 14:38
S47	23	isostatic adj bond\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/10/30 14:43
S48	2	("5207864").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/02/27 10:23
S49	2	("7,276,789").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/02/27 10:35

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